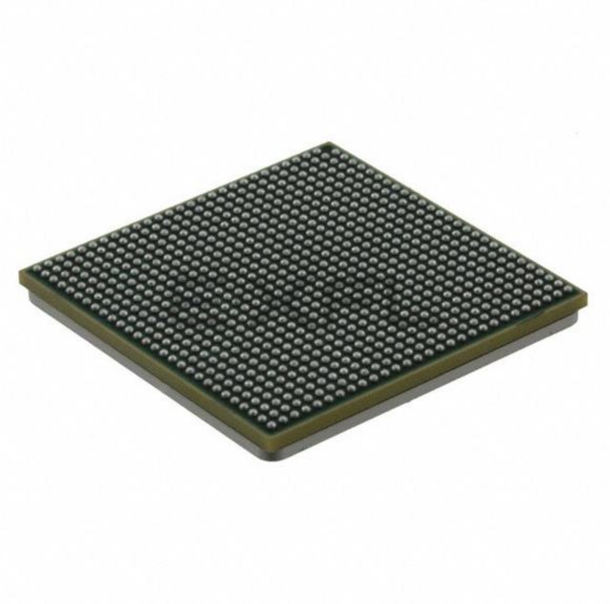

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8544eavtalf

    - Two key (K1, K2, K1) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES
  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Two protocol engines available on a per chip select basis:

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 35	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45 (default) 45 (default) 125	BV_{DD} = 3.3 V BV_{DD} = 2.5 V BV_{DD} = 1.8 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	42 (default)		
DDR signal	20	GV_{DD} = 2.5 V	—
DDR2 signal	16 32 (half strength mode)	GV_{DD} = 1.8 V	—
TSEC signals	42	LV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	42	OV_{DD} = 3.3 V	—
I^2C	150	OV_{DD} = 3.3 V	—

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.

2.2 Power Sequencing

The device requires its power rails to be applied in specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DD_n}, BV_{DD}, LV_{DD}, SV_{DD}, OV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

Note that all supplies must be at their stable values within 50 ms.

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power up, then the sequencing for GV_{DD} is not required.

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

4.2 Real-Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2 × the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

4.3 eTSEC Gigabit Reference Clock Timing

Table 7 provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the MPC8544E.

Table 7. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV_{DD}, TV_{DD} = 2.5 V LV_{DD}, TV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV_{DD} = 2.5 V, and from 0.6 and 2.7 V for L/TVDD = 3.3 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 8.7.4, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 4.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 3.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 167 MHz.

4.5 Other Input Clocks

For information on the input clocks of other functional blocks of the platform such as SerDes, and eTSEC, see the specific section of this document.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the MPC8544E. Table 8 provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications[1]

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HREST}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:
1. SYSCLK is the primary clock input for the MPC8544E.

Table 9 provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
Core and platform PLL lock times	—	100	µs	—
Local bus PLL	—	50	µs	—
PCI bus lock time	—	50	µs	—

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8544E. Note that DDR SDRAM is GV_{DD}(typ) = 2.5 V and DDR2 SDRAM is GV_{DD}(typ) = 1.8 V.

6.1 DDR SDRAM DC Electrical Characteristics

Table 10 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8544E when GV_{DD}(typ) = 1.8 V.

Table 10. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.26$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.24$	V	—
Output high current (V_{OUT} = 1.26 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.33 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

Table 11 provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 12 provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 12. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.31$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.3$	V	—
Output high current (V_{OUT} = 1.8 V)	I_{OH}	–16.2	—	mA	—

Table 12. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current (V_{OUT} = 0.42 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

Table 13 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the current draw characteristics for MV_{REF}.

Table 14. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 15 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

8.5.2 GMII AC Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.5.2.1 GMII Transmit AC Timing Specifications

Table 30 provides the GMII transmit AC timing specifications.

Table 30. GMII Transmit AC Timing Specifications

At recommended operating conditions with L/TVDD of 3.3 V ± 5% or 2.5 V ± 5%

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.2	—	5.0	ns	2
GTX_CLK data clock rise time (20%-80%)	t_{GTXR}	—	—	1.0	ns	—
GTX_CLK data clock fall time (80%-20%)	t_{GTXF}	—	—	1.0	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Data valid t_{GTKHDV} to GTX_CLK Min setup time is a function of clock period and max hold time (Min setup = cycle time – Max delay).

Figure 13 shows the GMII transmit AC timing diagram.

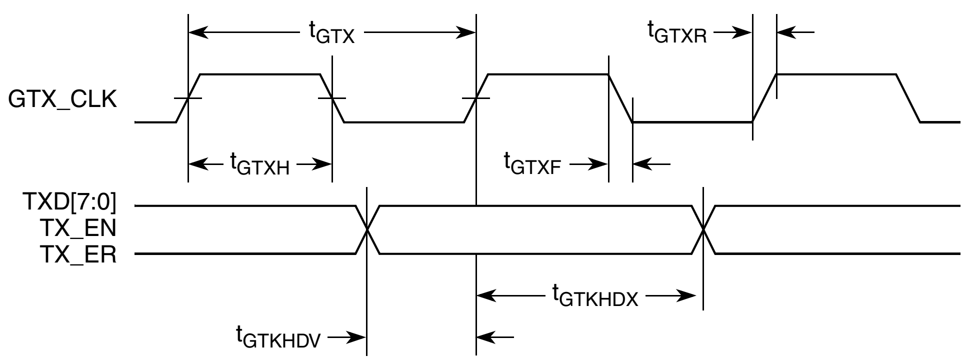


Figure 13. GMII Transmit AC Timing Diagram

Table 46. Local Bus General Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.6	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 2.5-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

Table 47 describes the general timing parameters of the local bus interface at BV_{DD} = 1.8 V DC.

Table 47. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	2.6	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t_{LBOTOT}	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	3.2	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	3.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	3.2	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.9	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.9	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.6	ns	5

Figure 28 through Figure 33 show the local bus signals.

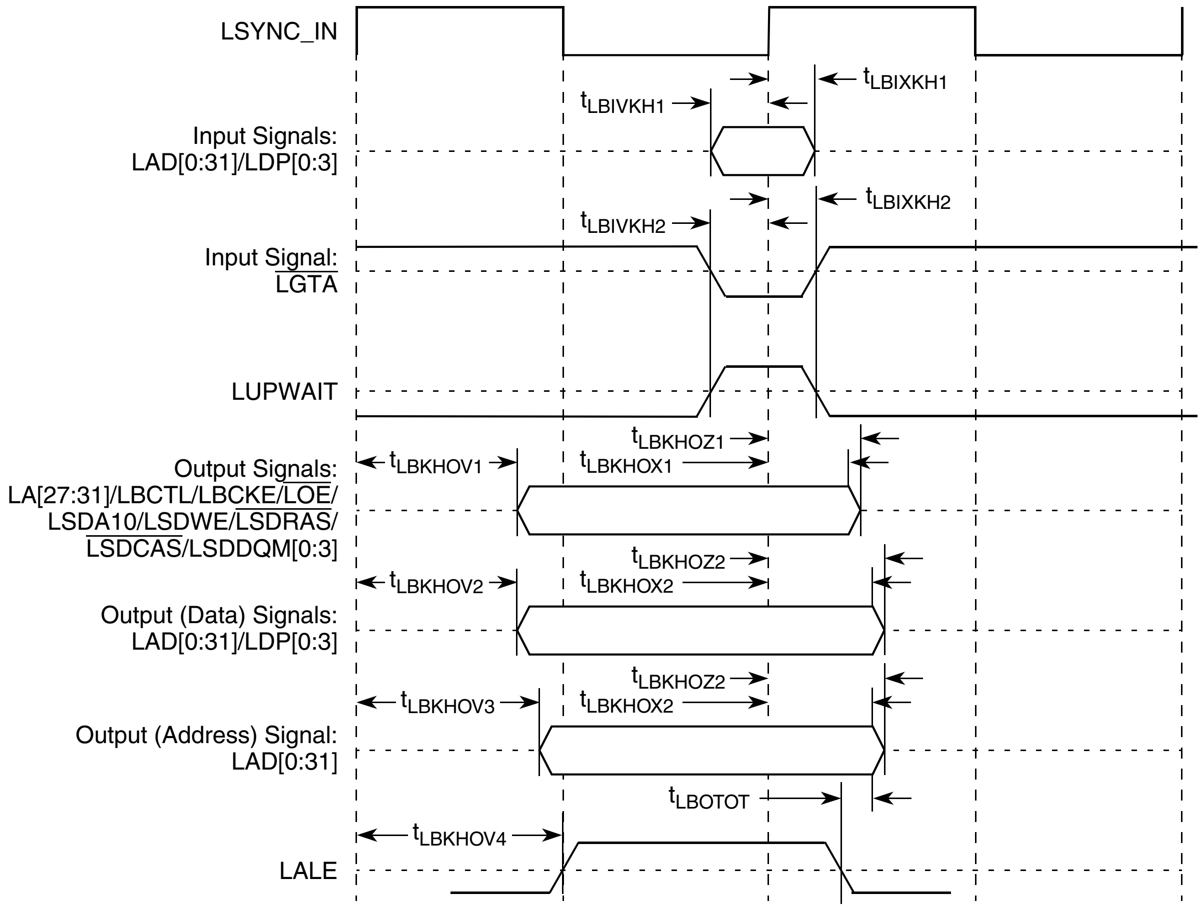


Figure 28. Local Bus Signals (PLL Enabled)

Table 48 describes the general timing parameters of the local bus interface at V_{DD} = 3.3 V DC with PLL disabled.

Table 48. Local Bus General Timing Parameters—PLL Bypassed

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	12	—	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
Internal launch/capture clock to LCLK delay	t_{LBKHKT}	1.2	4.9	ns	—
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	7.4	—	ns	4, 5
LUPWAIT input setup to local bus clock	$t_{LBIVKL2}$	6.75	—	ns	4, 5
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	–0.2	—	ns	4, 5
LUPWAIT input hold from local bus clock	$t_{LBIXKL2}$	–0.2	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKLOV1}$	—	1.6	ns	—

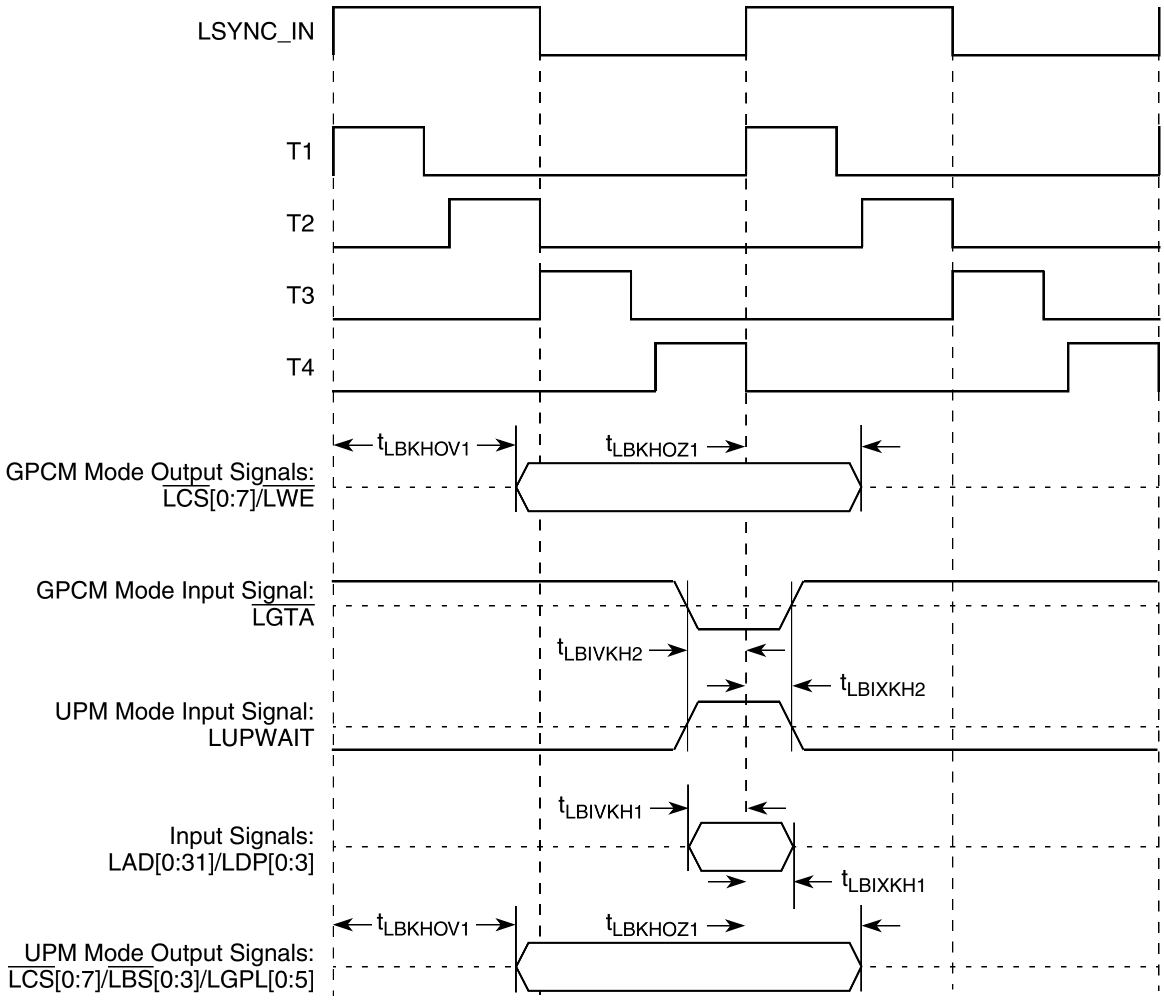


Figure 32. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Enabled)

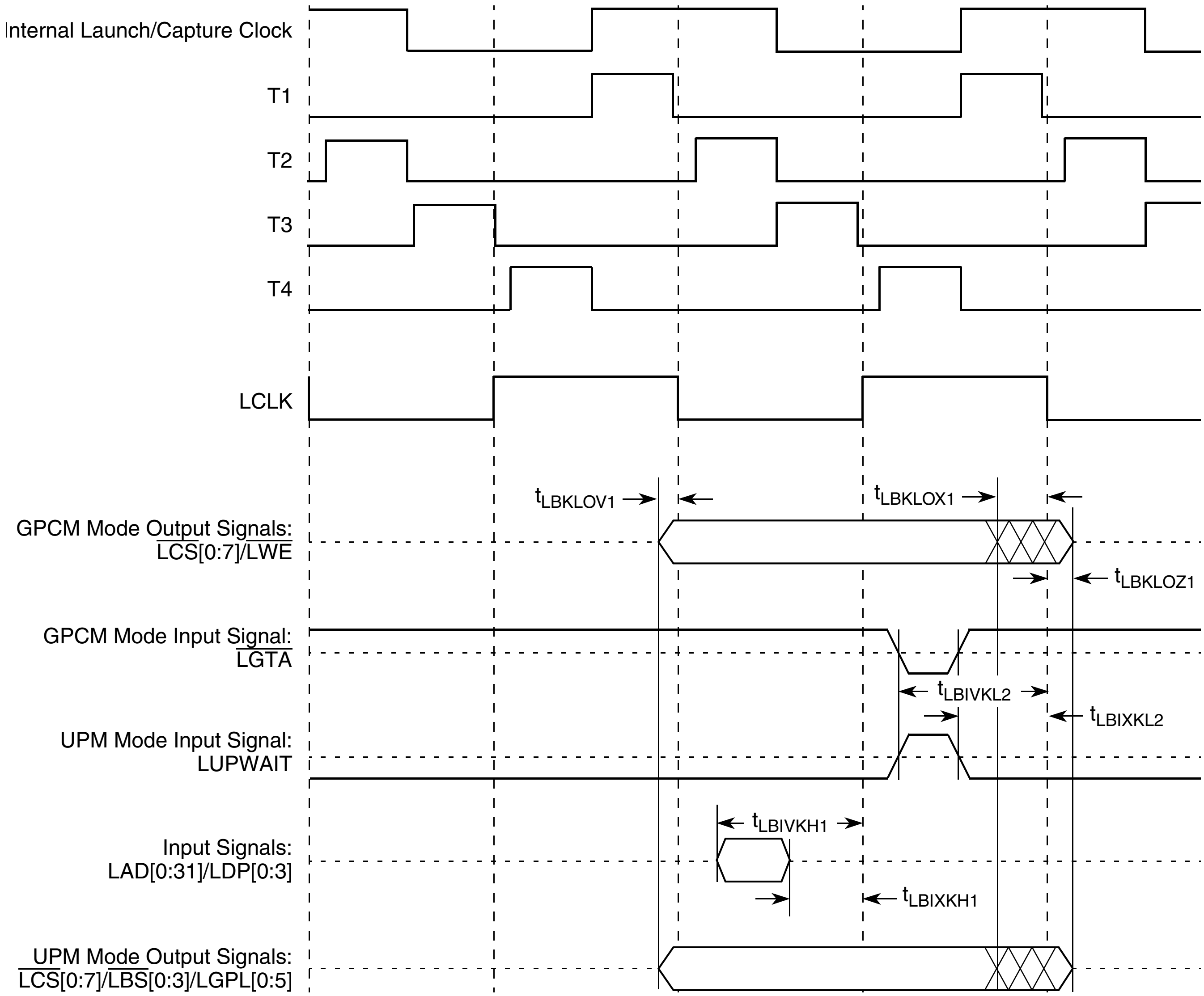


Figure 33. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

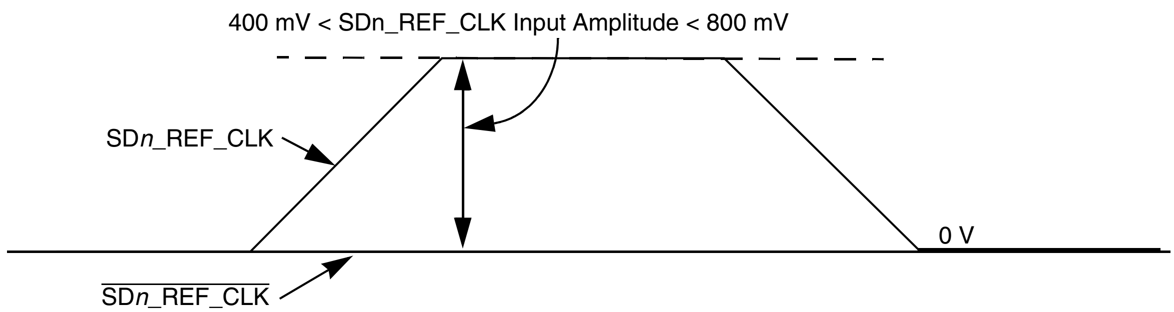


Figure 48. Single-Ended Reference Clock Input DC Requirements

16.2.3 Interfacing With Other Differential Signaling Levels

With on-chip termination to SGND_SRDS*n* (xcorevss), the differential reference clocks inputs are HCSL (high-speed current steering logic) compatible DC-coupled.

Many other low voltage differential type outputs like LVDS (low voltage differential signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 to 400 mV) for DC-coupled connection.

LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

NOTE

Figure 49 through Figure 52 are for conceptual reference only. Due to the fact that clock driver chip's internal structure, output impedance and termination requirements are different between various clock driver chip manufacturers, it is very possible that the clock circuit reference designs provided by clock driver chip vendor are different from what is shown below. They might also vary from one vendor to the other. Therefore, Freescale Semiconductor can neither provide the optimal clock driver reference circuits, nor guarantee the correctness of the following clock driver connection reference circuits. The system designer is recommended to contact the selected clock driver chip vendor for the optimal reference circuits with the MPC8544E SerDes reference clock receiver requirement provided in this document.

16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

Table 57 describes some AC parameters common to SGMII, and PCI Express protocols.

Table 57. SerDes Reference Clock Common AC Parameters

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V_{IH}	+200	—	mV	2
Differential Input Low Voltage	V_{IL}	—	–200	mV	2
Rising edge rate (SD*n*_REF_CLK) to falling edge rate ($\overline{\mathrm{SD}n\_\mathrm{REF\_CLK}}$) matching	Rise-Fall Matching	—	20	%	1, 4

Notes:

1. Measurement taken from single ended waveform.
2. Measurement taken from differential waveform.
3. Measured from –200 mV to +200 mV on the differential waveform (derived from SD*n*_REF_CLK minus $\overline{\mathrm{SD}n\_\mathrm{REF\_CLK}}$). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 53.
4. Matching applies to rising edge rate for SD*n*_REF_CLK and falling edge rate for $\overline{\mathrm{SD}n\_\mathrm{REF\_CLK}}$. It is measured using a 200 mV window centered on the median cross point where SD*n*_REF_CLK rising meets $\overline{\mathrm{SD}n\_\mathrm{REF\_CLK}}$ falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of SD*n*_REF_CLK should be compared to the fall edge rate of $\overline{\mathrm{SD}n\_\mathrm{REF\_CLK}}$, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 54.

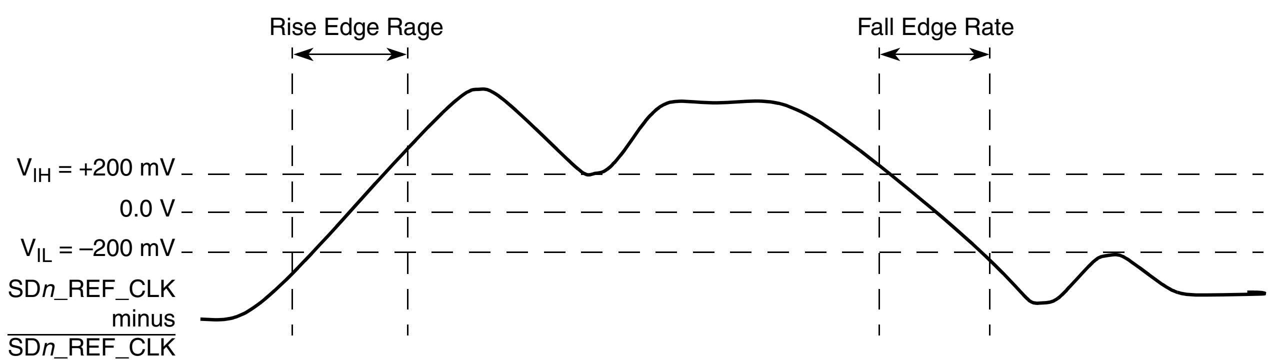


Figure 53. Differential Measurement Points for Rise and Fall Time

Table 60. Differential Receiver (RX) Input Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Units	Comments
$T_{RX\text{-}EYE\text{-}MEDIAN\text{-}to\text{-}MAX\text{-}JITTER}$	Maximum time between the jitter median and maximum deviation from the median	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX\text{-}DIFFp\text{-}p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.
$V_{RX\text{-}CM\text{-}ACp}$	AC peak common mode input voltage	—	—	150	mV	$V_{RX\text{-}CM\text{-}ACp} = \lvert V_{RXD+} - V_{RXD-}\rvert \div 2 - V_{RX\text{-}CM\text{-}DC}$ $V_{RX\text{-}CM\text{-}DC} = DC_{(avg)}$ of $\lvert V_{RX\text{-}D+} - V_{RX\text{-}D-}\rvert/2$ See Note 2.
$RL_{RX\text{-}DIFF}$	Differential return loss	15	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at +300 and –300 mV, respectively. See Note 4.
$RL_{RX\text{-}CM}$	Common mode return loss	6	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at 0 V. See Note 4.
$Z_{RX\text{-}DIFF\text{-}DC}$	DC differential input impedance	80	100	120	Ω	RX DC differential mode impedance. See Note 5.
$Z_{RX\text{-}DC}$	DC input impedance	40	50	60	Ω	Required RX D+ as well as D– DC impedance (50 ± 20% tolerance). See Notes 2 and 5.
$Z_{RX\text{-}HIGH\text{-}IMP\text{-}DC}$	Powered down DC input impedance	200 k	—	—	Ω	Required RX D+ as well as D– DC impedance when the receiver terminations do not have power. See Note 6.
$V_{RX\text{-}IDLE\text{-}DET\text{-}DIFFp\text{-}p}$	Electrical idle detect threshold	65	—	175	mV	$V_{RX\text{-}IDLE\text{-}DET\text{-}DIFFp\text{-}p} = 2 \times \lvert V_{RX\text{-}D+} - V_{RX\text{-}D-}\rvert$ Measured at the package pins of the receiver.
$T_{RX\text{-}IDLE\text{-}DET\text{-}DIFF\text{-}ENTERTIME}$	Unexpected electrical idle enter detect threshold integration time	—	—	10	ms	An unexpected electrical idle ($V_{RX\text{-}DIFFp\text{-}p} < V_{RX\text{-}IDLE\text{-}DET\text{-}DIFFp\text{-}p}$) must be recognized no longer than $T_{RX\text{-}IDLE\text{-}DET\text{-}DIFF\text{-}ENTERING}$ to signal an unexpected idle condition.

18.3 Pinout Listings

Table 62 provides the pinout listing for the MPC8544E 783 FC-PBGA package.

NOTE

The naming convention of TSEC1 and TSEC3 is used to allow the splitting voltage rails for the eTSEC blocks and to ease the port of existing PowerQUICC III software.

NOTE

The $\overline{\text{DMA\_DACK}}$[0:1] and $\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. Please refer to Table 62 for more details.

Table 62. MPC8544E Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
PCI1_AD[31:0]	AE8, AD8, AF8, AH12, AG12, AB9, AC9, AE9, AD10, AE10, AC11, AB11, AB12, AC12, AF12, AE11, Y14, AE15, AC15, AB15, AA15, AD16, Y15, AB16, AF18, AE18, AC17, AE19, AD19, AB17, AB18, AA16	I/O	OV_{DD}	—
PCI1_C_$\overline{\text{BE}}$[3:0]	AC10, AE12, AA14, AD17	I/O	OV_{DD}	—
$\overline{\text{PCI1\_GNT}}$[4:1]	AE7, AG11,AH11, AC8	O	OV_{DD}	4, 8, 24
$\overline{\text{PCI1\_GNT0}}$	AE6	I/O	OV_{DD}	—
$\overline{\text{PCI1\_IRDY}}$	AF13	I/O	OV_{DD}	2
PCI1_PAR	AB14	I/O	OV_{DD}	—
$\overline{\text{PCI1\_PERR}}$	AE14	I/O	OV_{DD}	2
$\overline{\text{PCI1\_SERR}}$	AC14	I/O	OV_{DD}	2
$\overline{\text{PCI1\_STOP}}$	AA13	I/O	OV_{DD}	2
$\overline{\text{PCI1\_TRDY}}$	AD13	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AF9, AG10, AH10, AD6	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AB8	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	—
$\overline{\text{PCI1\_DEVSEL}}$	AC13	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AD12	I/O	OV_{DD}	2
PCI1_IDSEL	AG6	I	OV_{DD}	—

Table 62. MPC8544E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{SD2\_REF\_CLK}}$	AF2	I	XV_{DD}	—
SD2_TST_CLK	AG4	—	—	—
$\overline{\text{SD2\_TST\_CLK}}$	AF4	—	—	—
General-Purpose Output				
GPOUT[0:7]	AF22, AH23, AG27, AH25, AF21, AF25, AG26, AF26	O	OV_{DD}	—
General-Purpose Input				
GPIN[0:7]	AH24, AG24, AD23, AE21, AD22, AF23, AG25, AE20	I	OV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG16	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG15	O	OV_{DD}	21
$\overline{\text{SRESET}}$	AG19	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AH5	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA12	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AC5	I	OV_{DD}	—
TRIG_OUT/READY/ $\overline{\text{QUIESCE}}$	AB5	O	OV_{DD}	5, 8, 15, 21
MSRCID[0:1]	Y7, W9	O	OV_{DD}	4, 5, 8
MSRCID[2:4]	AA9, AB6, AD5	O	OV_{DD}	5, 15, 21
MDVAL	Y8	O	OV_{DD}	5
CLK_OUT	AE16	O	OV_{DD}	10
Clock				
RTC	AF15	I	OV_{DD}	—
SYSCLK	AH16	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	11
TDO	AF28	O	OV_{DD}	10
TMS	AH27	I	OV_{DD}	11
$\overline{\text{TRST}}$	AH22	I	OV_{DD}	11

19.5 Security Controller PLL Ratio

Table 67 shows the SEC frequency ratio.

Table 67. SEC Frequency Ratio

Signal Name	Value (Binary)	CCB CLK:SEC CLK
LWE_B	0	2:1[1]
	1	3:1[2]

Notes:

1. In 2:1 mode the CCB frequency must be operating ≤ 400 MHz.
2. In 3:1 mode any valid CCB can be used. The 3:1 mode is the default ratio for security block.

19.6 Frequency Options

19.6.1 SYSCLK to Platform Frequency Options

Table 68 shows the expected frequency values for the platform frequency when using a CCB clock to SYSCLK ratio in comparison to the memory bus clock speed.

Table 68. Frequency Options of SYSCLK with Respect to Memory Bus Speeds

CCB to SYSCLK Ratio	SYSCLK (MHz)						
	33.33	41.66	66.66	83	100	111	133.33
	Platform /CCB Frequency (MHz)						
2							—
3					—	333	400
4			—	333	400	445	533
5			333	415	500		
6			400	500			
8		333	533				
9		375					
10	333	417					
12	400	500					
16	533						

20.3 Thermal Management Information

This section provides thermal management information for the flip chip plastic ball grid array (FC-PBGA) package for air-cooled applications. Proper thermal control design is primarily dependent on the system-level design—the heat sink, airflow, and thermal interface material. The MPC8544E implements several features designed to assist with thermal management, including the temperature diode. The temperature diode allows an external device to monitor the die temperature in order to detect excessive temperature conditions and alert the system; see Section 20.3.4, "Temperature Diode," for more information.

The recommended attachment method to the heat sink is illustrated in Figure 61. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

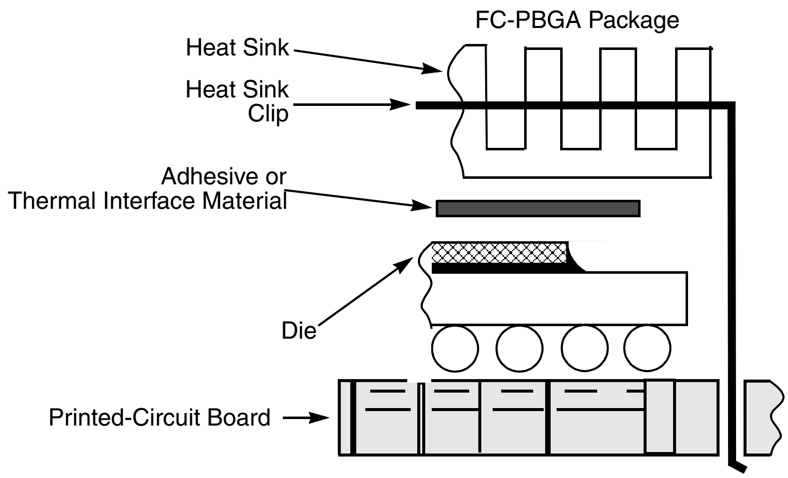


Figure 61. Package Exploded Cross-Sectional View with Several Heat Sink Options

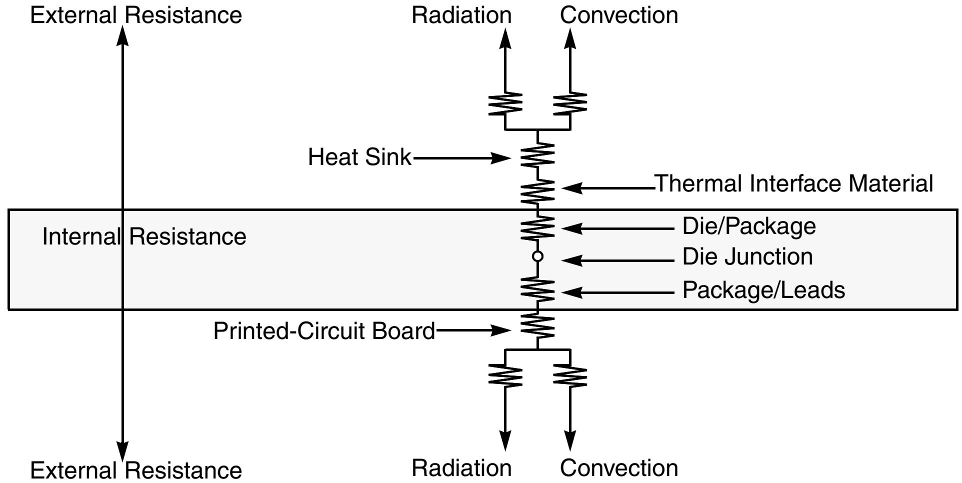
The system board designer can choose between several types of heat sinks to place on the device. There are several commercially-available heat sinks from the following vendors:

Aavid Thermalloy603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Advanced Thermal Solutions781-769-2800
89 Access Road #27.
Norwood, MA02062
Internet: www.qats.com

Alpha Novatech408-567-8082
473 Sapena Ct. #12
Santa Clara, CA 95054
Internet: www.alphanovatech.com

Figure 62 depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance.)

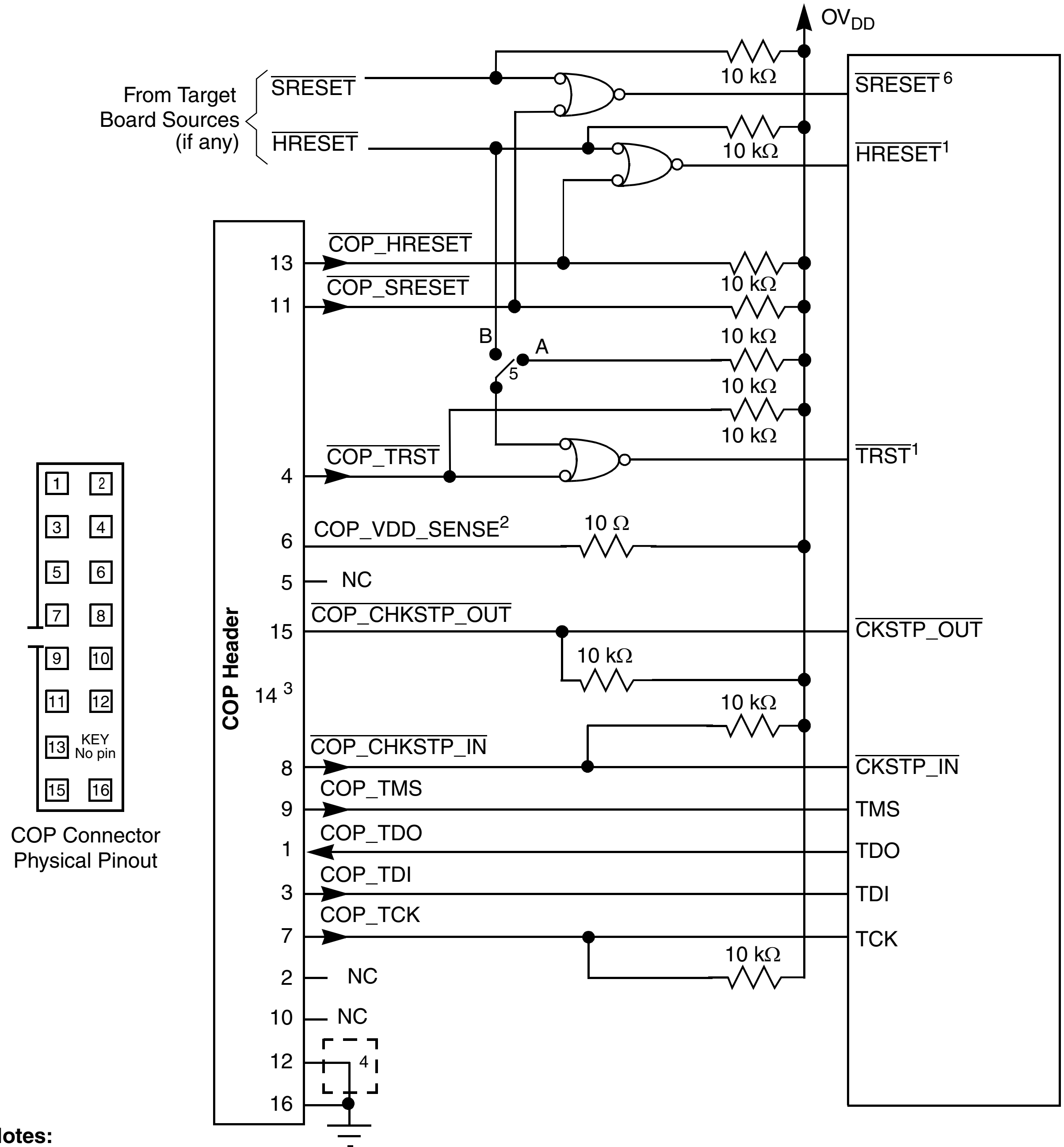
Figure 62. Package with Heat Sink Mounted to a Printed-Circuit Board

The heat sink removes most of the heat from the device. Heat generated on the active side of the chip is conducted through the silicon and through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

20.3.2 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. For those applications where the heat sink is attached by spring clip mechanism, Figure 63 shows the thermal performance of three thin-sheet thermal-interface materials (silicone, graphite/oil, floroether oil), a bare joint, and a joint with thermal grease as a function of contact pressure. As shown, the performance of these thermal interface materials improves with increasing contact pressure. The use of thermal grease significantly reduces the interface thermal resistance. The bare joint results in a thermal resistance approximately six times greater than the thermal grease joint.

Figure 69 shows the JTAG interface connection.



Notes:

1. The COP port and target board should be able to independently assert $\overline{\text{HRESET}}$ and $\overline{\text{TRST}}$ to the processor in order to fully control the processor as shown here.
2. Populate this with a 10-Ω resistor for short-circuit/current-limiting protection.
3. The KEY location (pin 14) is not physically present on the COP header.
4. Although pin 12 is defined as a No Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
5. This switch is included as a precaution for BSDL testing. The switch should be closed to position A during BSDL testing to avoid accidentally asserting the $\overline{\text{TRST}}$ line. If BSDL testing is not being performed, this switch should be closed to position B.
6. Asserting $\overline{\text{SRESET}}$ causes a machine check interrupt to the e500 core.

Figure 69. JTAG Interface Connection